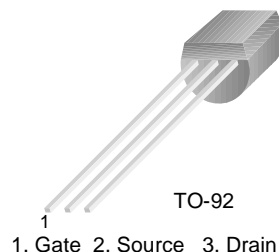


2N5245

2N5245

N-Channel RF Amplifier

- This device is designed for HF/VHF mixer/amplifier and applications where process 50 is not adequate. Sufficient gain and low noise for sensitive receivers.
- Sourced from process 90.



Absolute Maximum Ratings* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DG}	Drain-Gate Voltage	30	V
V_{GS}	Gate-Source Voltage	-30	V
I_{GF}	Forward Gate Current	10	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 ~ 150	$^\circ\text{C}$

* This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- These rating are based on a maximum junction temperature of 150 degrees C.
- These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	$I_G = 1.0\mu\text{A}, V_{DS} = 0$	-30		V
I_{GSS}	Gate Reverse Current	$V_{GS} = 25\text{V}, V_{DS} = 0$		-1.0	nA
$V_{GS(off)}$	Gate-Source Cutoff Voltage	$V_{DS} = 15\text{V}, I_D = 1.0\text{nA}$	-1.0	-0.6	V
On Characteristics					
I_{DSS}	Zero-Gate Voltage Drain Current *	$V_{DS} = 15\text{V}, V_{GS} = 0$	5	15	mA
Small Signal Characteristics					
gfs	Forward Transferconductance	$V_{GS} = 0\text{V}, V_{DS} = 15\text{V}, f = 1.0\text{kHz}$	4500	11000	μmhos
goss	Common- Source Output Conductance	$V_{GS} = 0\text{V}, V_{DS} = 15\text{V}, f = 1.0\text{kHz}$		50	μmhos

* Pulse Test: Pulse $\leq 300\mu\text{s}$

Thermal Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max.	Units
P_D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	$^\circ\text{C}/\text{W}$

Package Dimensions

2N5245

TO-92



Dimensions in Millimeters

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